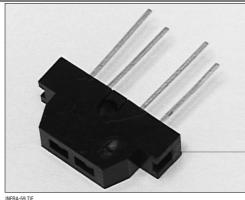
Reflective Sensor

FEATURES

- Phototransistor output
- Focused for maximum response
- · Low profile housing



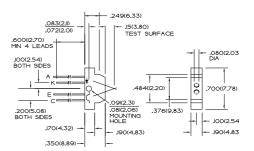
DESCRIPTION

The HOA0149 consists of an infrared emitting diode and an NPN silicon phototransistor encased side-byside on converging optical axes in a black thermoplastic housing. The phototransistor responds to radiation from the IRED only when a reflective object passes within its field of view. The HOA0149 employs plastic molded components. For additional component information see SEP8505 and SDP8405.

Housing material is ABS. Housings are soluble in chlorinated hydrocarbons and ketones. Recommended cleaning agents are methanol and isopropanol.

OUTLINE DIMENSIONS in inches (mm)

3 plc decimals ±0.010(0.25) 2 plc decimals ±0.020(0.51)



DIM_038.cdr



Reflective Sensor

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
IR EMITTER						
Forward Voltage	VF			1.6	V	I _F =20 mA
Reverse Leakage Current	I _R			10	μΑ	V _R =3 V
DETECTOR						
Collector-Emitter Breakdown Voltage	V _(BR) CEO	30			V	Ic=100 μA
Emitter-Collector Breakdown Voltage	V _{(BR)ECO}	5.0			V	I _E =100 μA
Collector Dark Current	Iceo			100	nA	V _{CE} =15 V, I _F =0
COUPLED CHARACTERISTICS On-State Collector Current HOA0149-001	Ic(on)	1.0			mA	VcE=5 V, Ir=40 mA
Collector-Emitter Saturation Voltage	VCE(SAT)			0.4	V	I _C =125 μA, I _F =40 mA ⁽¹⁾
Rise And Fall Time	t _r , t _f		15	·	μs	Vcc=5 V, Ic=1 mA

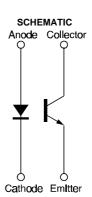
Notes
1. Test surface is a front surface mirror (polished aluminum, 85% reflectance) located 0.15 in.(3.80 mm) from the front surface of the

ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

Operating Temperature Range -40°C to 85°C -40°C to 85°C Storage Temperature Range Soldering Temperature (5 sec) 240°C IR EMITTER Power Dissipation 70 mW (1) 3 V

Reverse Voltage Continuous Forward Current 50 mA DETECTOR 30 V Collector-Emitter Voltage Emitter-Collector Voltage 70 mW (1) Power Dissipation



Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

Collector DC Current

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30 mA

Reflective Sensor

Fig. 1 IRED Forward Bias Characteristics

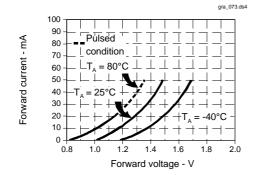


Fig. 2 Non-Saturated Switching Time vs Load Resistance gra_074.ds4

Load resistance - Ohms

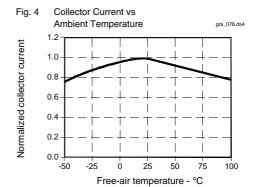
Fig. 3 Dark Current vs
Temperature

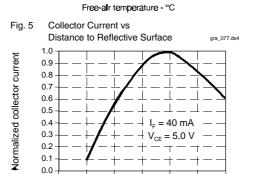
1000

VCE = 15 V
H = 0

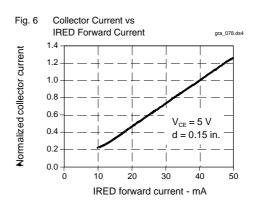
100

VCE = 15 V
H = 0





60



All Performance Curves Show Typical Values

0.10

0.15

Distance to reflective surface - inches

0.20

0.25

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0.1

-40

Reflective Sensor